

02N06Z

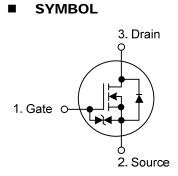
0.2A, 60V SILICON N-CHANNEL **MOSFET**

DESCRIPTION

The UTC **02N06Z** is a silicon N-channel MOSFET, it uses UTC's advanced technology to provide the customers with a minimum on state resistance, high switching speed and low gate charge.

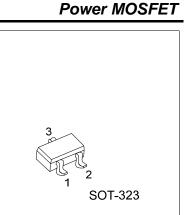
FEATURES

- * $R_{DS(ON)} \le 2.4\Omega$ @ $V_{GS}=10V$, $I_{D}=200mA$
- $R_{DS(ON)} \le 4.0\Omega @ V_{GS}=4V, I_D=200mA$
- * High switching speed
- * Low gate charge
- * High ESD



ORDERING INFORMATION

Ordering Number		Dookaac	Pin Assignment			Docking
Lead Free	Halogen Free	Package 1 2 3		Packing		
02N06ZL-AL3-R	02N06ZG-AL3-R	SOT-323	G	S	D	Tape Reel
Note: Pin Assignment: G: Gate S: Source D: Drain						
02N06ZG-AL3-R	 (1) R: Tape Reel (2) AL3: SOT-323 (3) G: Halogen Free and Lead Free, L: Lead Free 					
(3) G: Halogen Free and Lead Free, L:						
MARKING						
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■ **ABSOLUTE MAXIMUM RATINGS** (T_A = 25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT	
Drain-Source Voltage		V _{DSS}	60	V	
Gate-Source Voltage		V _{GSS}	±20	V	
Desia Orenant	Continuous	I _D	200	mA	
Drain Current	Pulsed (Note 2)	I _{DM}	800	mA	
Octomer Octomerat	Continuous	Is	200	mA	
Source Current	Pulsed (Note 2)	I _{SP}	800	mA	
Power Dissipation (Note 3)		PD	200	mW	
Channel Temperature		Т _{СН}	+150	°C	
Storage Temperature Range		T _{STG}	-55 ~ +150	°C	

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. $P_W \le 10\mu s$, Duty cycle $\le 1\%$

3. Each terminal mounted on a recommended

ELECTRICAL CHARACTERISTICS (T_A = 25°C, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS		TYP	MAX	UNIT
OFF CHARACTERISTICS			•				
Drain-Source Breakdown Voltage		BV _{DSS}	I _D =10μA, V _{GS} =0V	60			V
Drain-Source Leakage Current		I _{DSS}	V _{DS} =60V, V _{GS} =0V			1	μA
Gate-Source Leakage Current	Forward	lass	V _{GS} =+20V, V _{DS} =0V			+10	μA
	Reverse	I _{GSS}	V _{GS} =-20V, V _{DS} =0V			-10	μA
ON CHARACTERISTICS							
Gate Threshold Voltage		V _{GS(TH)}	V _{DS} =10V, I _D =1mA			2.5	V
Static Drain-Source On-State Resistance (Note 2)		R _{DS(ON)}	V _{GS} =10V, I _D =200mA		1.7	2.4	Ω
			V _{GS} =4V, I _D =200mA		2.8	4.0	Ω
Forward Transfer Admittance (Note 2)		Y _{FS}	V _{DS} =10V, I _D =200mA 100				mS
DYNAMIC PARAMETERS						-	
Input Capacitance		CISS			15		рF
Output Capacitance		C _{oss}	V _{GS} =0V, V _{DS} =10V, f=1.0MHz		8		рF
Reverse Transfer Capacitance		C _{RSS}			4		рF
SWITCHING PARAMETERS (N	lote 3)			_		-	
Total Gate Charge		Q_{G}			2.2	4.4	nC
Gate to Source Charge		Q_{GS}	V _{GS} =10V, V _{DD} =30V, I _D =200mA		0.6		nC
Gate to Drain Charge		Q_{GD}			0.3		nC
Turn-ON Delay Time		t _{D(ON)}			6		ns
Rise Time		t _R	V_{DD} =30V, V_{GS} =10V, I_D =100mA, R _{GS} =10 Ω , R _L =300 Ω		5		ns
Turn-OFF Delay Time		t _{D(OFF)}			12		ns
Fall-Time		t _F			95		ns

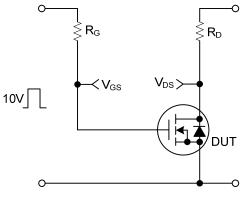
Notes: 1. $P_W \le 300 \mu s$, Duty cycle $\le 1\%$

2. Pulsed

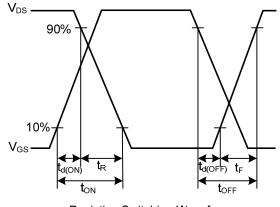


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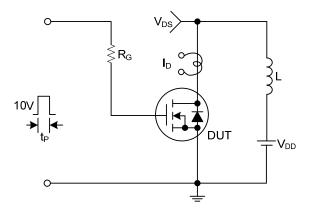
TEST CIRCUITS AND WAVEFORMS



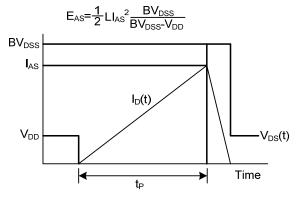
Resistive Switching Test Circuit



Resistive Switching Waveforms



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms



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